

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	2007	(257/637 or 257/642 or 257/734). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:26
L1	1877	(257/637 or 257/742 or 257/734). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:26
S9	34	semiconductor and (organic near7 polybenzoxazole) and (dielectric and insulat\$3) and @ad<"20021203"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:27
S8	788	semiconductor and (organic near10 (dielectric and insulat\$3)) and @ad<"20021203" and (bond or pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:27
S7	1688	semiconductor and (organic near10 (dielectric and insulat\$3)) and @ad<"20021203"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:27
S5	616	semiconductor and hall and organic and (dielectric and insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:27
L4	729	semiconductor and hall and organic and (dielectric and insulat\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:27
L9	172	semiconductor and (organic with polybenzoxazole) and (dielectric or insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:28
L8	114	semiconductor and (organic with polybenzoxazole) and (dielectric and insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:28
L7	79	semiconductor and (organic with polybenzoxazole) and (dielectric and insulat\$3) and @ad<"20021203"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:28
L6	1226	semiconductor and (organic near10 (dielectric and insulat\$3)) and (bond or pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:28
L12	1134	semiconductor and (organic near10 (dielectric or insulat\$3)) and (bond or pad or wiring) and seed\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:29

L11	18666	semiconductor and (organic near10 (dielectric or insulat\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:29
L10	7685	semiconductor and (organic near10 (dielectric or insulat\$3)) and (bond or pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:29
L5	2526	semiconductor and (organic near10 (dielectric and insulat\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:29
L14	377	semiconductor and (organic near10 (dielectric or insulat\$3)) and ((bond or pad or wiring) same seed\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:31
L13	201	semiconductor and (organic near10 (dielectric or insulat\$3)) and ((bond or pad or wiring) with seed\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:31
L2	1467	(257/753 or 257/759 or 257/760). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 22:55
L16	1807	semiconductor and (seed\$5 same (bond\$4 or pad)).	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 23:04
L18	785	semiconductor and (seed\$5 with (bond\$4 or pad)) and (insulat\$5 or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 23:05
L17	1494	semiconductor and (seed\$5 same (bond\$4 or pad)) and (insulat\$5 or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 23:05
L19	280	semiconductor and ((seed\$5 with (bond\$4 or pad)) same (insulat\$5 or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 23:48
L15	50	(257/753 or 257/759 or 257/760 or 257/637 or 257/642 or 257/734).ccls. and (seed\$5 same (bond\$4 or pad))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 23:48
L21	817	(257/753 or 257/759 or 257/760 or 257/637 or 257/642 or 257/734).ccls. and ((bond\$4 or pad) same (insulat\$4 or dielectric)) and @ad<"20021230"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 23:49

L20	971	(257/753 or 257/759 or 257/760 or 257/637 or 257/642 or 257/734).ccls. and ((bond\$4 or pad) same (insulat\$4 or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/03 23:49
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